

MOSFETs Silicon N-Channel MOS (DTMOSVI)

TK200V65Z5

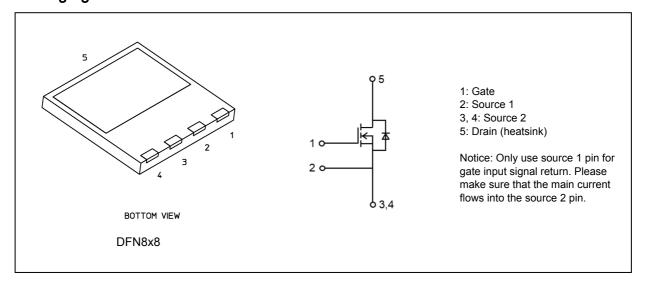
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Fast reverse recovery time: $t_{rr} = 95$ ns (typ.)
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 0.154 \Omega$ (typ.)
- (3) High-speed switching properties with lower capacitance.
- (4) Enhancement mode: $V_{th} = 3.5 \text{ to } 4.5 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 0.61 \text{ mA)}$

3. Packaging and Internal Circuit



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4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Rating | Unit | |
|--|----------|------------------|------------|----|
| Drain-source voltage | | V_{DSS} | 650 | V |
| Gate-source voltage | | V _{GSS} | ±30 | |
| Drain current (DC) | (Note 1) | I _D | 15 | Α |
| Drain current (pulsed) | (Note 1) | I _{DP} | 60 | |
| Power dissipation $(T_c = 25 ^{\circ}C)$ | | P_{D} | 130 | W |
| Single-pulse avalanche energy | (Note 2) | E _{AS} | 204 | mJ |
| Single-pulse avalanche current | | I _{AS} | 3 | Α |
| Reverse drain current (DC) | (Note 1) | I _{DR} | 15 | |
| Reverse drain current (pulsed) | (Note 1) | I _{DRP} | 60 | |
| Channel temperature | | T _{ch} | 150 | °C |
| Storage temperature | | T _{stg} | -55 to 150 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|------------------------------------|-----------------------|-------|------|
| Channel-to-case thermal resistance | R _{th(ch-c)} | 0.961 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 40.2 mH, I_{AS} = 3 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|-------|-------|------|
| Gate leakage current | I _{GSS} | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±1 | μΑ |
| Drain cut-off current | I _{DSS} | V _{DS} = 650 V, V _{GS} = 0 V | 1 | _ | 100 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 650 | _ | _ | V |
| Gate threshold voltage | V_{th} | V _{DS} = 10 V, I _D = 0.61 mA | 3.5 | _ | 4.5 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = 10 V, I _D = 7.5 A | - | 0.154 | 0.200 | Ω |



6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|----------|--------------------|---|-----|------|-----|------|
| Input capacitance | | C _{iss} | V _{DS} = 300 V, V _{GS} = 0 V, f = 100 kHz | _ | 1400 | _ | pF |
| Reverse transfer capacitance | | C _{rss} | | _ | 1.2 | _ | |
| Output capacitance | | C _{oss} | | _ | 38 | _ | |
| Effective output capacitance (energy related) | (Note 3) | C _{o(er)} | V _{DS} = 0 to 400 V, V _{GS} = 0 V | _ | 58 | _ | |
| Effective output capacitance (time related) | (Note 4) | C _{o(tr)} | | _ | 375 | _ | |
| Gate resistance | | r _g | V _{DS} = OPEN , f = 1 MHz | _ | 2.8 | _ | Ω |
| Switching time (rise time) | | t _r | See Fig. 6.2.1 | _ | 10 | _ | ns |
| Switching time (turn-on time) | | t _{on} | | _ | 35 | _ | |
| Switching time (fall time) | | t _f | | _ | 4.4 | _ | |
| Switching time (turn-off time) | | t _{off} | | _ | 60 | _ | |
| MOSFET dv/dt ruggedness | | dv/dt | $V_{DS} \leq V_{DSS}, \ I_D \leq 7.5 \ A$ | 90 | _ | _ | V/ns |

Note 3: $C_{O(er)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 V to 400 V. Note 4: $C_{O(tr)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 V to 400 V.

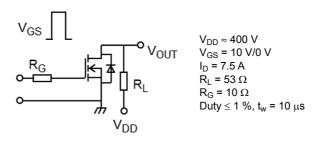


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$ | 1 | 26 | | nC |
| Gate-source charge 1 | Q _{gs1} | | _ | 8.8 | _ | |
| Gate-drain charge | Q_{gd} | | _ | 8.8 | _ | |

6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------|--------------------|---|-----|------|------|------|
| Diode forward voltage | V _{DSF} | I _{DR} = 15 A, V _{GS} = 0 V | _ | _ | -1.7 | V |
| Reverse recovery time (Note | i) t _{rr} | V _{DD} = 400 V, | _ | 95 | 152 | ns |
| Reverse recovery charge | Q _{rr} | $I_{DR} = 7.5 \text{ A}, V_{GS} = 0 \text{ V}$ - $dI_{DR}/dt = 100 \text{ A/us}$ | _ | 0.4 | _ | μС |
| Peak reverse recovery current | Irr | -uiDR/ut = 100 A/μs | _ | 8.4 | _ | Α |
| Diode dv/dt ruggedness | dv/dt | $V_{DD} \le 400 \text{ V}, I_{DR} \le 7.5 \text{ A}, V_{GS} = 0 \text{ V}$ | 70 | | _ | V/ns |

Note 5: Defined by design.



7. Marking (Note)

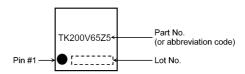


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.



8. Characteristics Curves (Note)

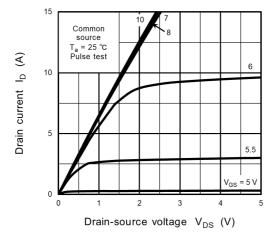


Fig. 8.1 I_D - V_{DS}

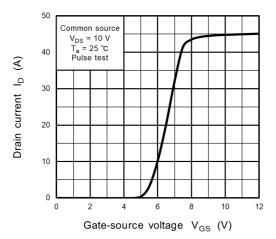


Fig. 8.3 ID - VGS

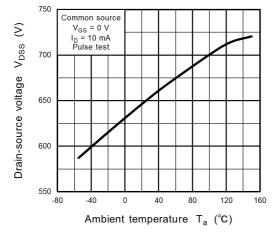


Fig. 8.5 V_{DSS} - T_a

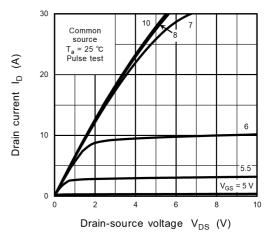


Fig. 8.2 I_D - V_{DS}

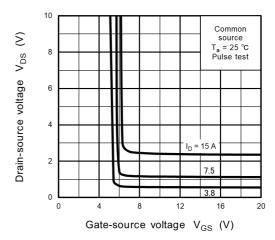


Fig. 8.4 V_{DS} - V_{GS}

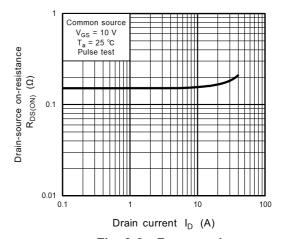
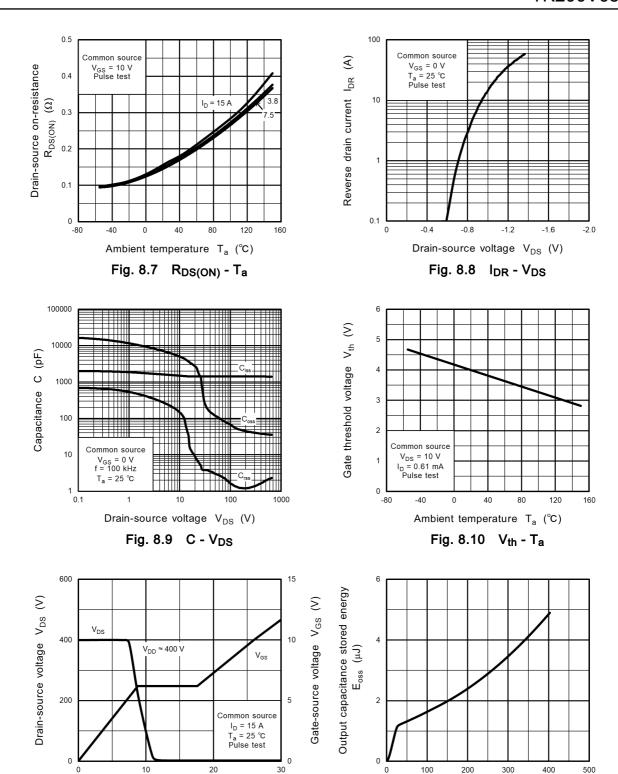


Fig. 8.6 $R_{DS(ON)}$ - I_D





Drain-source voltage V_{DS} (V) Fig. 8.12 Eoss - V_{DS}



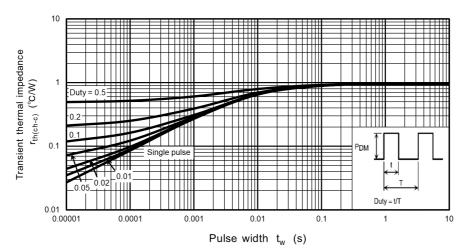
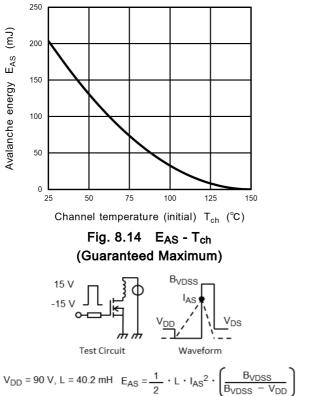


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)



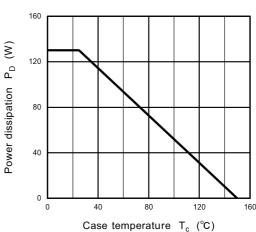


Fig. 8.15 $P_D - T_c$ (Guaranteed Maximum)

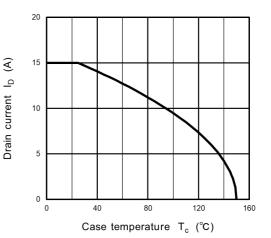


Fig. 8.16 Test Circuit/Waveform

Fig. 8.17 I_D - T_c (Guaranteed Maximum)

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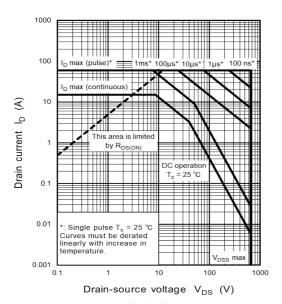


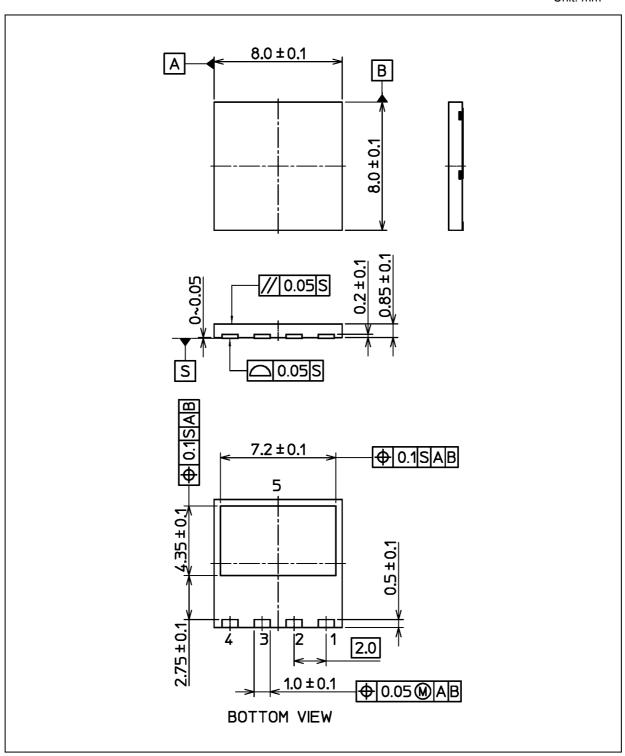
Fig. 8.18 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.175 g (typ.)

| | Package Name(s) |
|------------------|-----------------|
| TOSHIBA: 2-8T1A | |
| Nickname: DFN8x8 | |



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